

FCW65D20D1Q

eSiC Silicon Carbide Schottky Diode

650V, 20A



Description

The 650V eSiC is an advanced Faster Semiconductor's silicon carbide diode family. This technology combines the benefits of excellent low capacitive charge and robustness. Consequently, the eSiC family is suitable for application requiring high power efficiency.

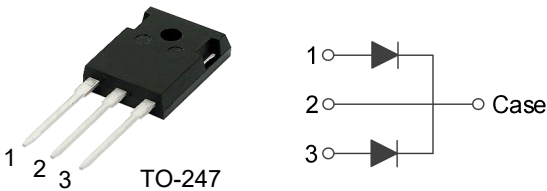
Applications

- Power Factor Correction
- Industrial Power Supplies
- Solar Inverter, UPS

Features

V_{RRM}	I_F	$T_{J,max}$	Q_C
650 V	10 / 20 A	175 °C	31 nC

- No reverse recovery current
- Low capacitive charge
- 175°C Max junction temperature
- High surge current capability
- Switching behavior independent of temperature
- Pb-Free, Halogen Free and RoHS compliant



Absolute Maximum Ratings (Per Leg / Device & Per Leg, $T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		650	V
I_F	Forward Current	$T_C=136^{\circ}\text{C}$	10 / 20	A
$I_{F,SM}$	Non-Repetitive Forward Surge Current	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ ms}$	50	A
		$T_C=150^{\circ}\text{C}$, $t_p=10\text{ ms}$	42.5	A
$I_{F,Max}$	Non-Repetitive Peak Forward Current	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ us}$	424	A
		$T_C=150^{\circ}\text{C}$, $t_p=10\text{ us}$	360	A
$I^2dt\text{ value}$	$\int i^2 dt$	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ ms}$	12.5	A^2s
		$T_C=150^{\circ}\text{C}$, $t_p=10\text{ ms}$	9	A^2s
P_{tot}	Power Dissipation	$T_C=25^{\circ}\text{C}$	75	W
T_J, T_{STG}	Operating Junction and Storage Temperature		-55 to +175	$^{\circ}\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.(Per Leg / Per Device)	2.0 / 1.0	$^{\circ}\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Marking	Package	Packing Method	Quantity
FCW65D20D1Q	FCW65D20D1Q	TO-247	Tube	30 units

Electrical Characteristics (Per Leg, T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F =10 A, T _C =25°C		1.40	1.7	V
		I _F =10 A, T _C =175°C		1.55	-	
I _R	Reverse Current	V _R =650 V, T _C =25°C		-	100	μA
		V _R =650 V, T _C =175°C		-	300	
Q _C	Total Capacitive Charge	V _R =400 V, T _C =25°C		31		nC
C	Total Capacitance	V _R =1 V, f=100 kHz		505		pF
		V _R =400 V, f=100 kHz		49		
E _C	Capacitance Stored Energy	V _R =400 V, T _C =25°C		4.6		μJ

Typical Performance Characteristics (Per Leg)

Figure 1. Power Derating

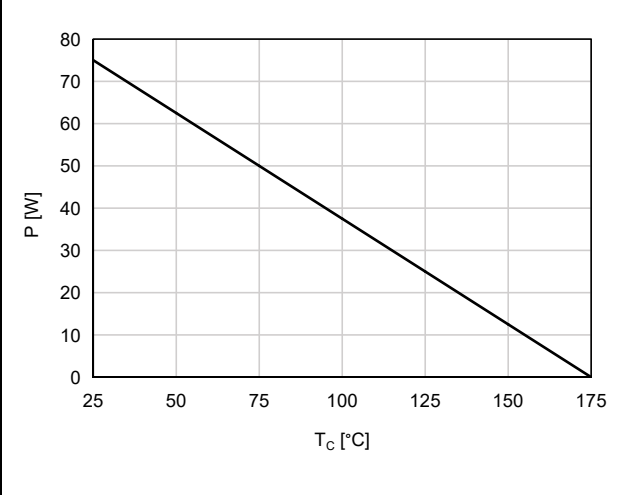


Figure 2. Current Derating

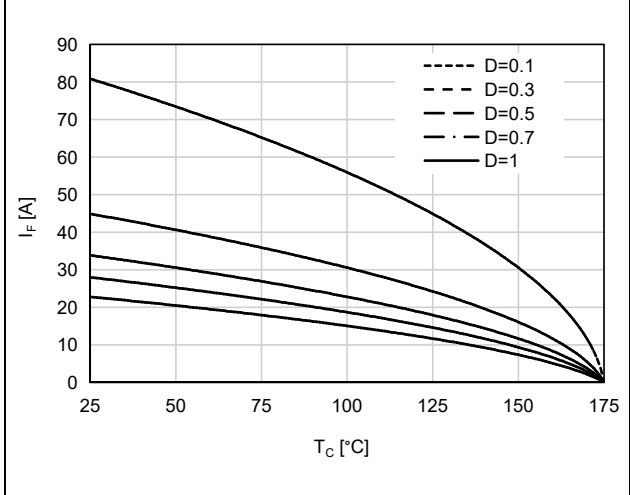


Figure 3. Forward Characteristics

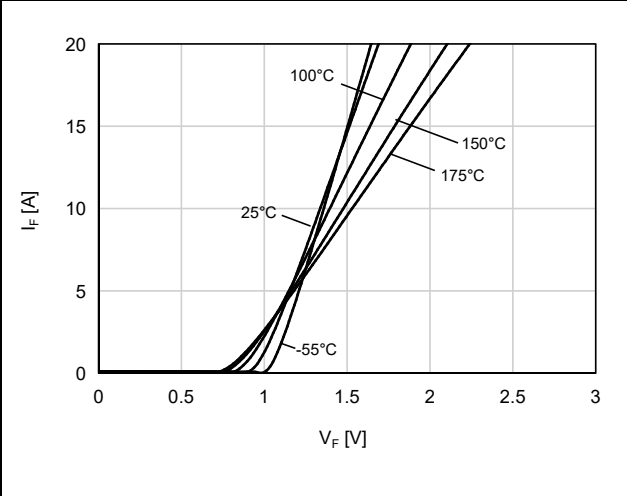


Figure 4. Reverse Characteristics

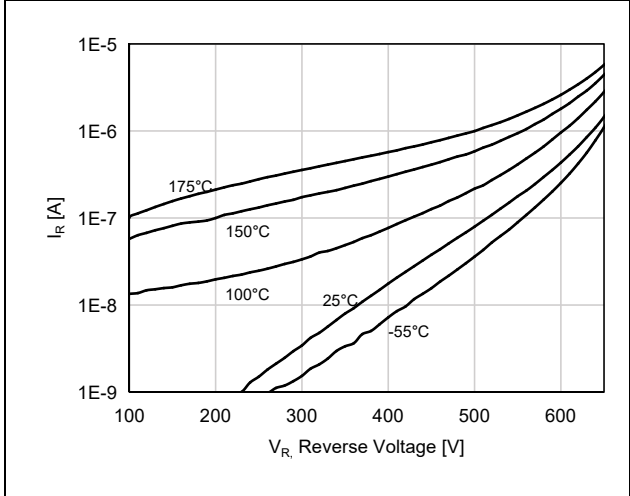


Figure 5. Capacitive Charge Characteristic

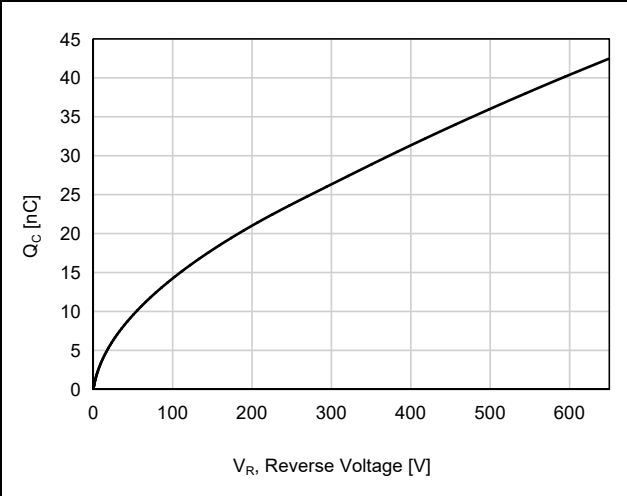
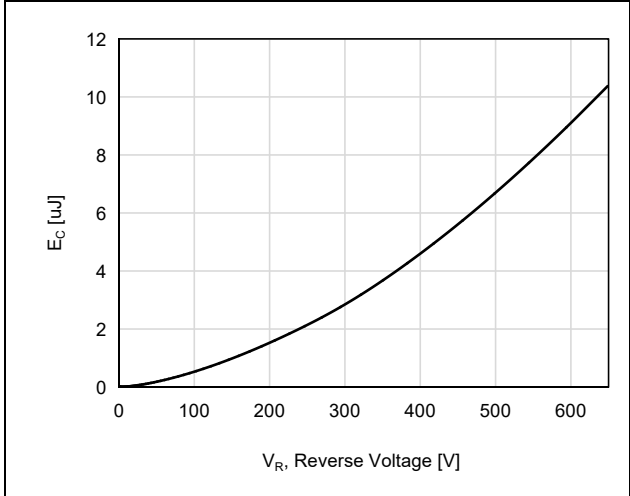


Figure 6. Capacitance Stored Energy



Typical Performance Characteristics (Per Leg)

Figure 7. Capacitance Characteristic

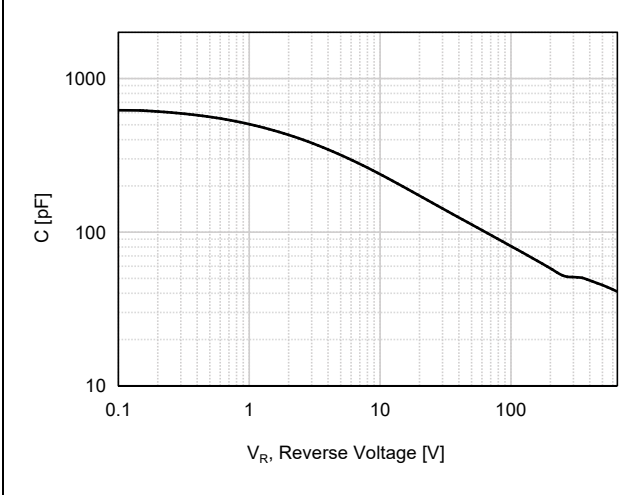
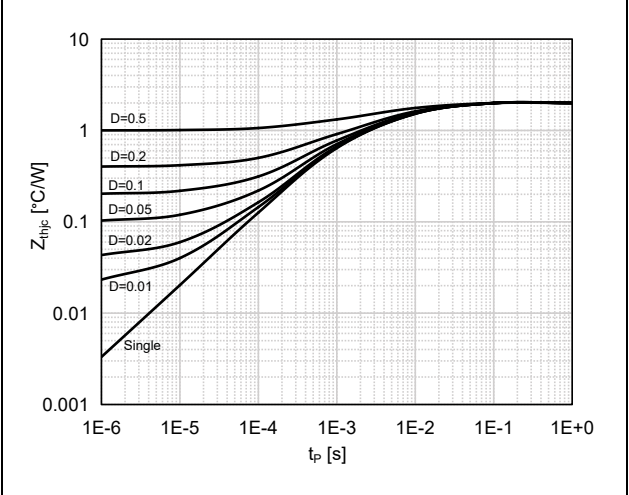
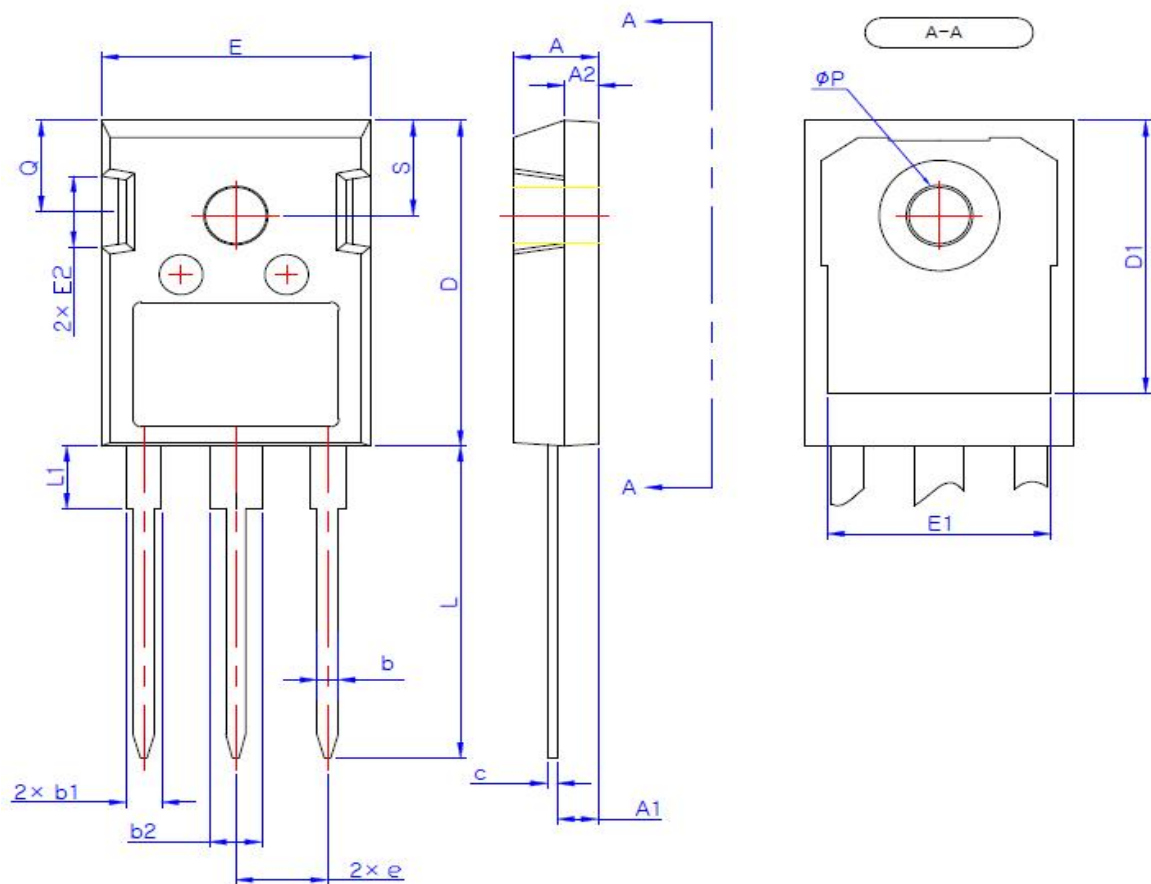


Figure 8. Transient Thermal Response Curve



Package Outlines

TO-247



SYMBOL	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.29	2.42	2.54
A2	1.90	2.00	2.10
b	1.10	1.20	1.30
b1	1.91	2.06	2.20
b2	2.92	3.06	3.20
c	0.50	0.60	0.70
D	20.80	21.07	21.34
D1	17.43	17.63	17.83
E	15.75	15.94	16.13
E1	13.06	13.26	13.46
E2	4.32	4.58	4.83
e	5.45 BSC		
L	19.85	20.05	20.25
L1	4.05	4.27	4.49
ΦP	3.55	3.60	3.65
Q	5.59	5.89	6.19
S	6.15 BSC		

* Dimensions in millimeters